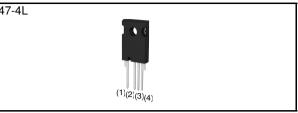


# SCT4062KRHR

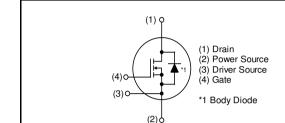
Automotive Grade N-channel SiC power MOSFET

V <sub>DSS</sub>	1200V
R <sub>DS(on)</sub> (Typ.)	62mΩ
$I_{D}^{*1}$	26A
P <sub>D</sub>	115W

#### Outline TO-247-4L



# Inner circuit



Please note Driver Source and Power Source are not exchangeable. Their exchange might lead to malfunction.

# Packaging specifications

	Packing	Tube
	Reel size (mm)	-
Tuno	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	30
	Taping code	C15
	Marking	SCT4062KR

# •Absolute maximum ratings (T<sub>vi</sub> = 25°C unless otherwise specified.)

	· ,				
Parameter		Symbol	Value	Unit	
Drain - source voltage		V <sub>DSS</sub>	1200	V	
Continuous drain		$T_c = 25^{\circ}C$	ı ı *1	26	Α
and source current	$V_{GS} = V_{GS_{on}}$	$T_c = 100^{\circ}C$	Ι <sub>D</sub> , Ι <sub>S</sub> <sup>*1</sup>	18	Α
Pulsed drain current	$V_{GS} = V_{GS\_on}$	$T_c = 25^{\circ}C$	I <sub>D,pulse</sub> *2	52	Α
Body diode pulsed forwa	ard current	$T_c = 25^{\circ}C$	1,*3 <sup>*1,*3</sup>	26	Α
Body diode surge forward current $V_{GS} = 0$		$V_{GS} = 0 V$	I <sub>S,pulse</sub> *1,*4	52	Α
Gate - source voltage (DC)		$V_{GSS_{DC}}$	-4 to +21	V	
Gate - source surge voltage (t <sub>surge</sub> < 300ns)		$V_{GSS\_surge}$ *5	-4 to +23	V	
Recommended turn-on gate - source drive voltage		$V_{GS_{on}}$ *6	+15 to +18	V	
Recommended turn-off gate - source drive voltage		V <sub>GS_off</sub>	0	V	
Virtual junction tempera	ture		T <sub>vj</sub>	175	°C
Range of storage temperature		T <sub>stg</sub>	-40 to +175	°C	

# Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating ; RoHS compliant

# Application

- Automobile
- · Switch mode power supplies

# •Electrical characteristics ( $T_{vj}$ = 25°C unless otherwise specified)

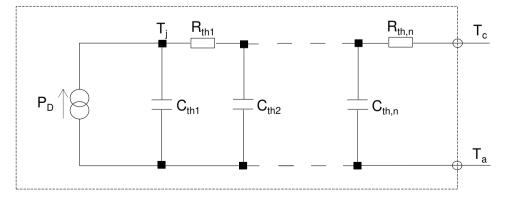
Deremeter	Cumphal	Conditions	Values			Linit	
Parameter	Symbol Conditions –		Min.	Тур.	Max.	Unit	
Drain - Source breakdown	V	$V_{GS} = 0 V, I_{D} = 5.3 mA$				V	
voltage	V (BR)DSS	$T_{vj} = 25^{\circ}C$	1200	-	-	V	
		$V_{GS} = 0 V, V_{DS} = 1200V$					
Zero Gate voltage Drain current	I <sub>DSS</sub>	$T_{vj} = 25^{\circ}C$	-	1	80	μA	
		T <sub>vj</sub> = 150°C	-	10	-		
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +21V$ , $V_{DS} = 0V$	-	-	100	nA	
Gate - Source leakage current		$V_{GS} = -4V  , V_{DS} = 0V$	-	-	-100	nA	
Gate threshold voltage	$V_{GS(th)}  {}^{*7}$	$V_{DS} = 10V, I_{D} = 6.45mA$	2.8	-	4.8	V	
		$V_{GS} = 18V, I_{D} = 12A$					
Static Drain - Source on - state resistance	${\sf R}_{\sf DS(on)}$ *8	T <sub>vj</sub> = 25°C	-	62	81	mΩ	
		$T_{vj} = 150^{\circ}C$	-	124	-		
Gate input resistance	R <sub>G</sub>	f = 1MHz, open drain	-	4	-	Ω	

#### Thermal resistance

Parameter	Symbol	Values			Unit
Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	${\sf R}_{\sf thJC}$ *9	-	0.98	1.3	K/W

# •Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R <sub>th1</sub>	8.4 ×10 <sup>-2</sup>		C <sub>th1</sub>	5.3 ×10 <sup>-4</sup>	
R <sub>th2</sub>	4.7 ×10 <sup>-1</sup>	K/W	C <sub>th2</sub>	2.4 ×10 <sup>-3</sup>	Ws/K
R <sub>th3</sub>	4.2 ×10 <sup>-1</sup>		C <sub>th3</sub>	4.3 ×10 <sup>-2</sup>	





# •Electrical characteristics ( $T_{vj}$ = 25°C unless otherwise specified)

Doromotor	Symbol	ymbol Conditions -		Values			
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Transconductance	g <sub>fs</sub> *8	$V_{DS} = 10V, I_{D} = 12A$	-	6.5	-	S	
Input capacitance	$C_{iss}$	$V_{GS} = 0V$	-	1498	-		
Output capacitance	$C_{oss}$	V <sub>DS</sub> = 800V	-	45	-	pF	
Reverse transfer capacitance	$C_{rss}$	f = 1MHz	-	3	-		
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0V$ $V_{DS} = 0V$ to 800V	-	54	-	pF	
Total Gate charge	Q <sub>g</sub> *8	V <sub>DS</sub> = 800V I <sub>D</sub> = 12A	-	64	-		
Gate - Source charge	Q <sub>gs</sub> *8	$V_{GS} = 18V$	-	14	-	nC	
Gate - Drain charge	Q <sub>gd</sub> *8	See Fig. 1-1, 1-2.	-	17	-		
Turn - on delay time	t <sub>d(on)</sub> *8	V <sub>DS</sub> = 800V I <sub>D</sub> = 12A	-	4.4	-		
Rise time	t <sub>r</sub> *8	V <sub>GS</sub> = +18V / 0V	-	11	-		
Turn - off delay time	t <sub>d(off)</sub> *8	$R_G = 0\Omega, L = 250\mu H$ E <sub>on</sub> includes diode	-	22	-	ns	
Fall time	t <sub>f</sub> *8	reverse recovery $L_{\sigma} = 50 \text{nH}, C_{\sigma} = 10 \text{pF}$	-	10	-		
Turn - on switching loss	E <sub>on</sub> *8	See Fig. 2-1, 2-2, 2-3.	-	132	-		
Turn - off switching loss	E <sub>off</sub> *8		-	6	-	μJ	



# •Body diode electrical characteristics (Source-Drain) (T<sub>vj</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Values	Unit	
Farameler	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	$V_{SD}^{*8}$	$V_{GS} = 0V, I_S = 12A$	-	3.3	-	V
Reverse recovery time	t <sub>rr</sub> *8	I <sub>F</sub> = 12A V <sub>B</sub> = 800V	-	8.1	-	ns
Reverse recovery charge	Q <sub>rr</sub> *8	v <sub>R</sub> = 800ν di/dt = 3800A/μs	-	105	-	nC
Peak reverse recovery current	I <sup>*8</sup>	$L_{\sigma} = 50$ nH, $C_{\sigma} = 10$ pF See Fig. 3-1, 3-2.	-	26	-	А

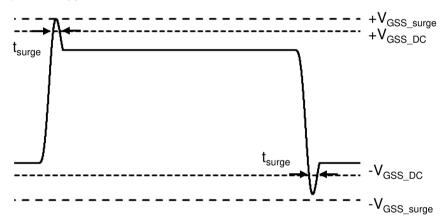
\*1 Limited by maximum  $T_{vj}$  and for Max.  $R_{thJC}$ .

\*2 Pulse width and duty cycle are limited by  $T_{vj,max}$ .

\*3 Only for body-diode, Repititive pulse, PW  $\leq$  1.5µs, Duty cycle  $\leq$  5%

\*4 When used as a protective function, PW  $\leq$  10µs

\*5 Example of acceptable V<sub>GS</sub> waveform



Please note especially when using driver source that  $V_{\text{GSS}\_surge}$  must be in the range of absolute maximum rating.

- \*6 Please be advised not to use SiC-MOSFETs with V<sub>GS</sub> below 10V as doing so may cause thermal runaway.
- \*7 Tested after applying  $V_{GS} = 21V$  for 100ms.
- \*8 Pulsed
- \*9 Measured conformable to JESD51-14.

See the application note "rthjc\_measurement\_and\_usage\_an-e.pdf". Link

 $URL: https://fscdn.rohm.com/en/products/databook/applinote/discrete/common/rthjc\_measurement\_and\_usage\_an-e.pdf$ 



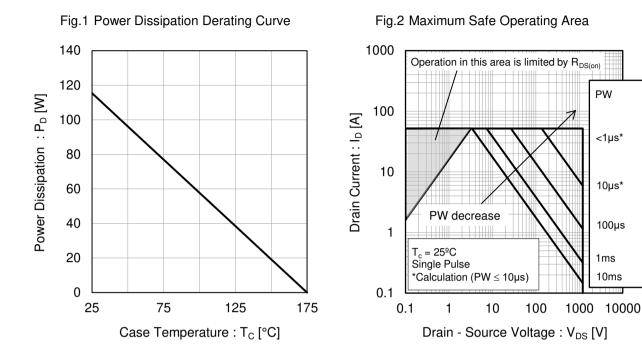
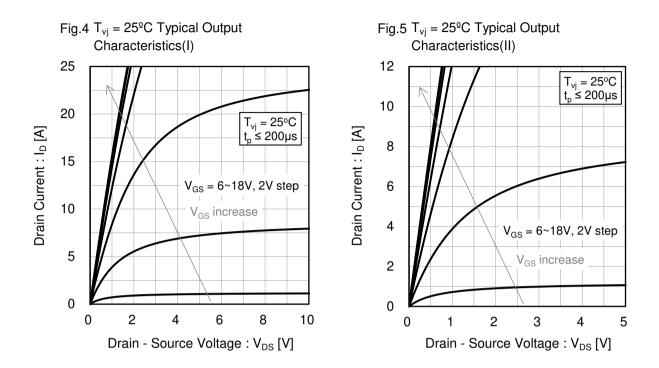


Fig.3 Typical Transient Thermal Impedance vs. Pulse Width 1 Transient Thermal Impedance : 0.1 Duty = 1 Z<sub>thJC</sub> [K/W] 0.5 0.01 0.2 Duty increase 0.1 0.05 0.001 0.02 0.01 Single pulse  $T_c = 25^{\circ}C$ 0.0001 1E-6 1E-5 1E-4 1E-3 1E-2 1E-1 1E+0 1E+1 Pulse Width : PW [s]

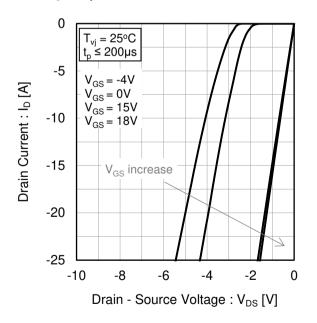
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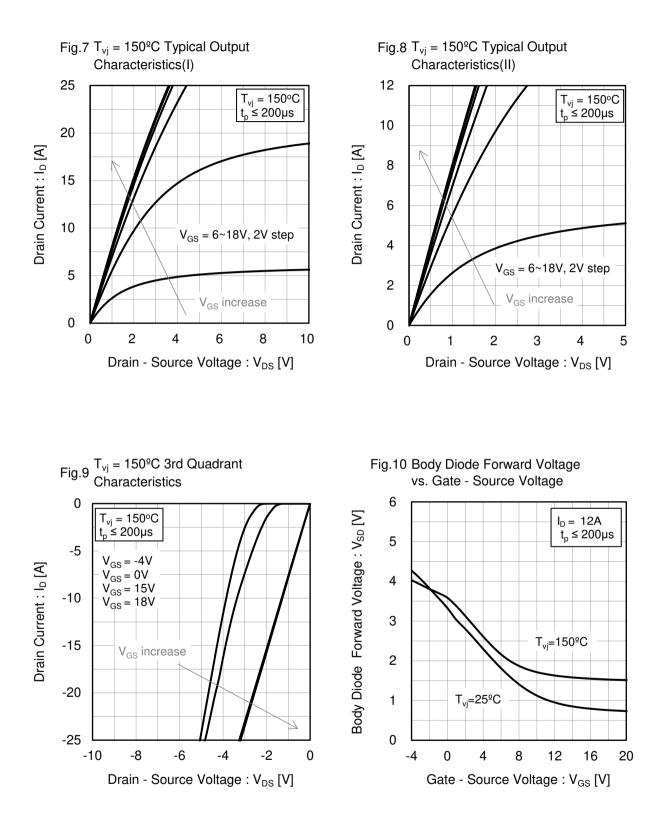


#### Fig.6 $T_{vj} = 25^{\circ}C$ 3rd Quadrant Characteristics



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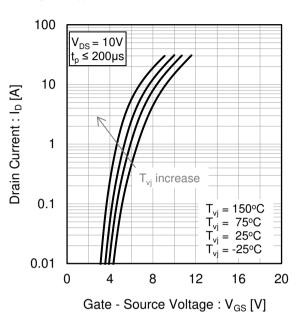
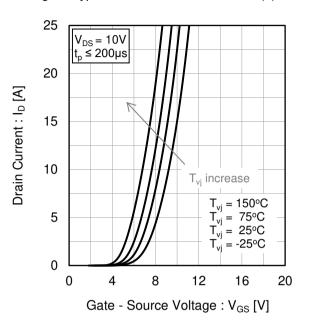


Fig.11 Typical Transfer Characteristics (I)

Fig.12 Typical Transfer Characteristics (II)



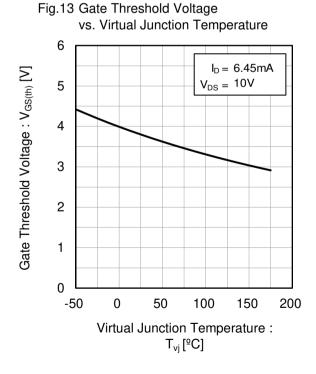
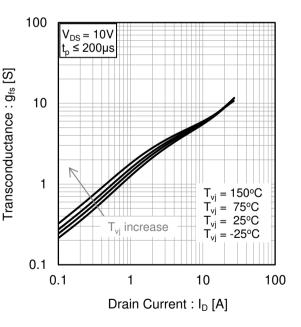
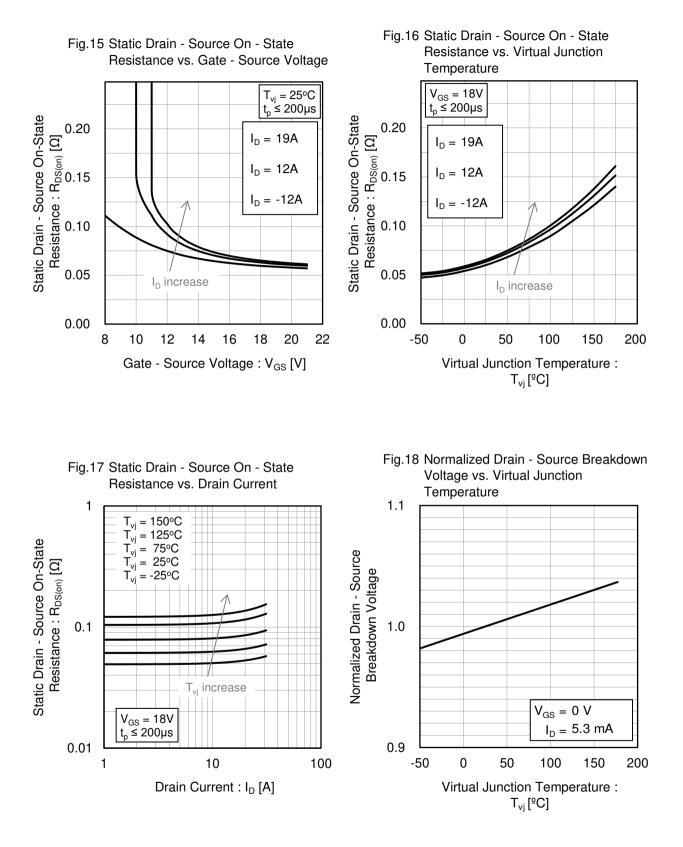


Fig.14 Transconductance vs. Drain Current

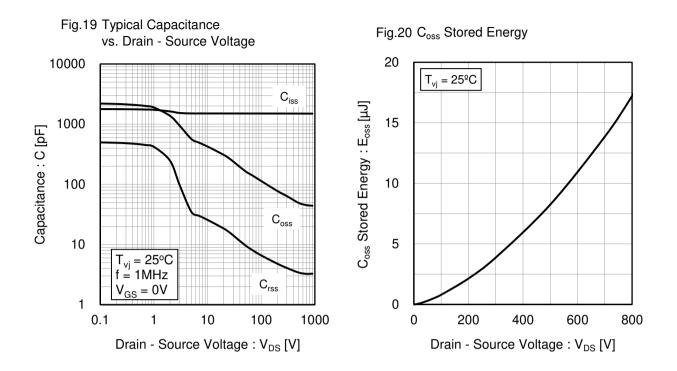


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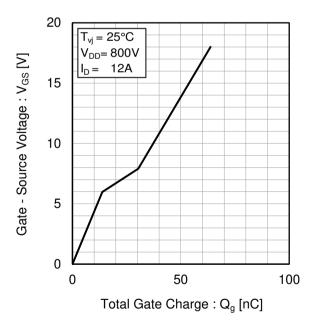




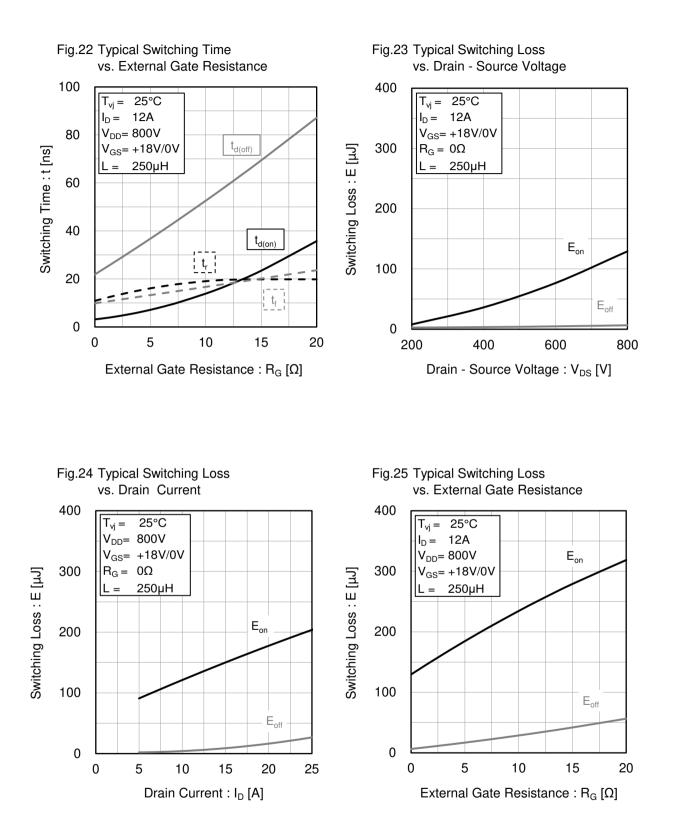




#### Fig.21 Dynamic Input Characteristics

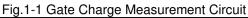


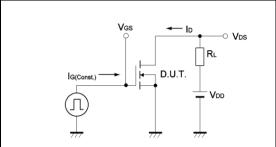




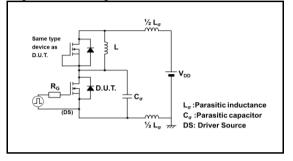


# Measurement circuits and waveforms





#### Fig.2-1 Switching Characteristics Measurement Circuit



# Fig.2-3 Waveforms for Switching Energy Loss

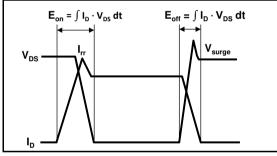
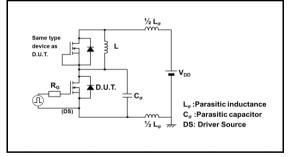
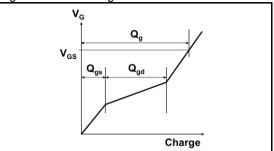


Fig.3-1 Reverse Recovery Time Measurement Circuit



#### Fig.1-2 Gate Charge Waveform





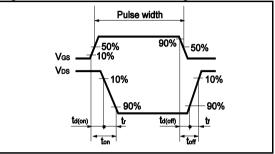
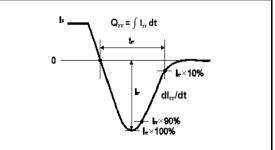


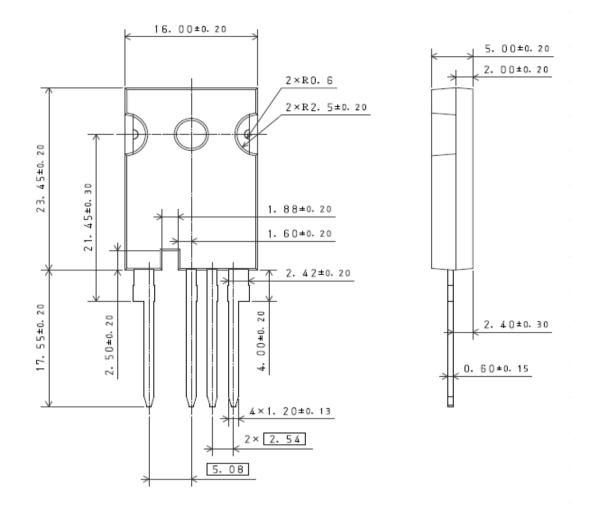
Fig.3-2 Reverse Recovery Waveform





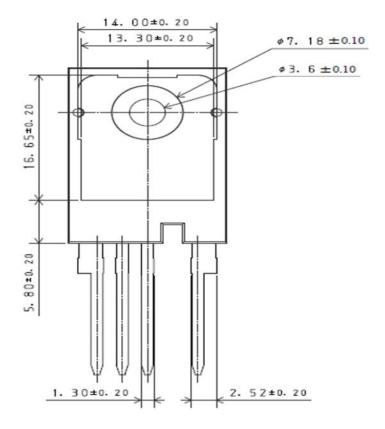
1.4±0.2

#### Package Dimensions



Unit: mm



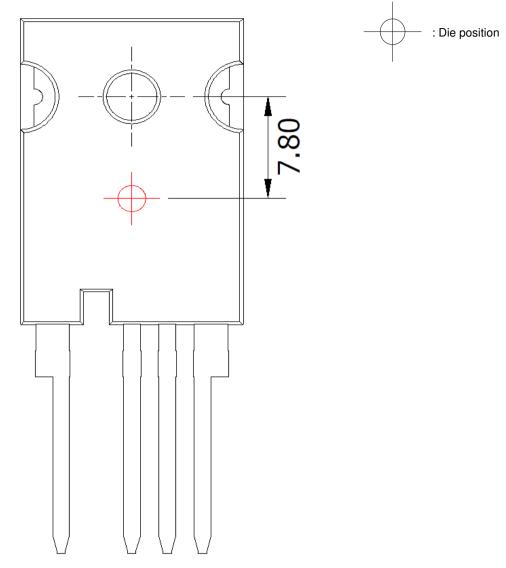


Unit: mm





## Die Bonding Layout



•Front view of the packaging.

•Dimensions are design values.

·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm



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